



### 150V N-Channel Enhancement Mode MOSFET

Voltage

150 V

Current

25 A

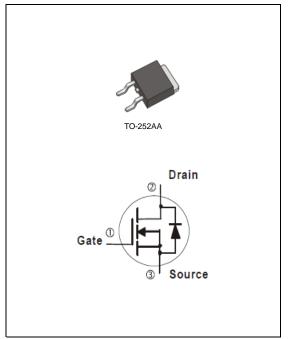
#### **Features**

- $R_{DS(ON)}$ ,  $V_{GS}@10V$ , $I_{D}@5A<65m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@6V$ ,  $I_{D}@3A<90m\Omega$
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS2.0 (2011/65/EU & 2015/865/EU directive)
- Green molding compound as per IEC61249 Std. (Halogen Free)

### **Mechanical Data**

• Case: TO-252AA Package

• Terminals: Solderable per MIL-STD-750, Method 2026



### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		$V_{DS}$	150	V	
Gate-Source Voltage		$V_{GS}$	<u>+</u> 25	V	
Continuous Drain Current	T <sub>C</sub> =25°C	I <sub>D</sub>	25		
	T <sub>C</sub> =100°C		16	A	
Pulsed Drain Current (Note 1)	T <sub>C</sub> =25°C	I <sub>DM</sub>	100		
Power Dissipation	T <sub>C</sub> =25°C	Po	102	10/	
	T <sub>C</sub> =100°C		41	W	
Continuous Drain Current	T <sub>A</sub> =25°C	I <sub>D</sub>	3.5	А	
	T <sub>A</sub> =70°C		2.8	А	
Power Dissipation	T <sub>A</sub> =25°C		2.0	101	
Power Dissipation	T <sub>A</sub> =70°C	Pb	1.3	W	
Single Pulse Avalanche Energy (Note 6)		E <sub>AS</sub>	242	mJ	
Operating Junction and Storage Temperature Range		$T_J$ , $T_{STG}$	-55~150	°C	
Typical Thermal Resistance <sup>(Note 4,5)</sup>	Junction to Case	$R_{ heta JC}$	1.23	0000	
	Junction to Ambient	$R_{\theta JA}$	62.5	°C/W	

<sup>•</sup> Limited only By Maximum Junction Temperature





### **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	$V_{GS}$ =0V, $I_D$ =250uA	150	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250$ uA	2.0	2.7	4.0	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	$V_{GS}$ =10V, $I_D$ =5A	-	50	65	mΩ
		$V_{GS}=6V,I_{D}=3A$	-	60	90	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =150V,V <sub>GS</sub> =0V	-	-	1.0	uA
Gate-Source Leakage Current	$I_{GSS}$	V <sub>GS</sub> = <u>+</u> 25V,V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	$Q_{g}$	V <sub>DS</sub> =75V, I <sub>D</sub> =4A, V <sub>GS</sub> =10V <sup>(Note 1,2)</sup>	-	29.5	-	nC
Gate-Source Charge	$Q_{gs}$		-	9.2	-	
Gate-Drain Charge	$Q_{gd}$		-	8.0	-	
Input Capacitance	Ciss	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, f=1.0MHZ	-	1764	-	pF
Output Capacitance	Coss		-	148	-	
Reverse Transfer Capacitance	Crss	I=I.UIVIMZ	-	62	-	
Turn-On Delay Time	td <sub>(on)</sub>	\/ 00\/ I 4A	-	14	-	
Turn-On Rise Time	t <sub>r</sub>	$V_{DS}=30V,I_{D}=1A,$ $V_{GS}=10V,R_{G}=6\Omega$ (Note 1.2)	-	21	-	ns
Turn-Off Delay Time	td <sub>(off)</sub>		-	32	-	
Turn-Off Fall Time	t <sub>f</sub>		-	23	-	
Drain-Source Diode						
Maximum Continuous Drain-Source			-	-	25	А
Diode Forward Current	I <sub>S</sub>					
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =1A,V <sub>GS</sub> =0V	-	0.7	1.0	V

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited.
- 5. R@JA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH,  $I_{AS}$ =22A,  $V_{DD}$ =50V,  $V_{GS}$ =10V
- 7. Guaranteed by design, not subject to production testing.





### **TYPICAL CHARACTERISTIC CURVES**

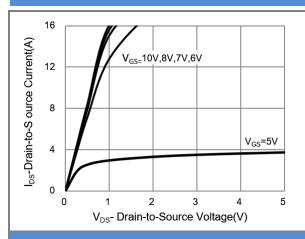
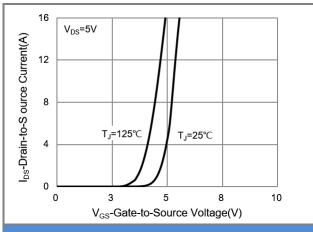


Fig.1 Output Characteristics



**Fig.2 Transfer Characteristics** 

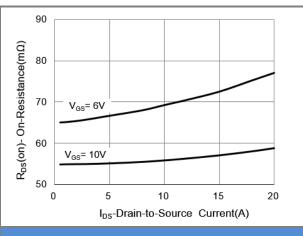


Fig.3 On-Resistance vs. Drain Current

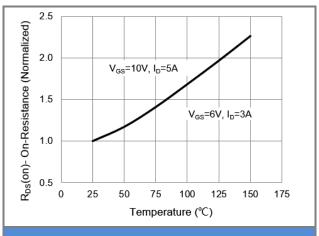


Fig.4 On-Resistance vs. Junction temperature

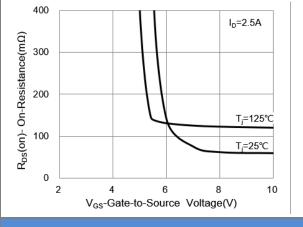


Fig.5 On-Resistance Variation with VGS.

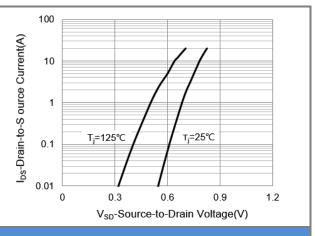


Fig.6 Source-Drain Diode Forward Voltage





### **TYPICAL CHARACTERISTIC CURVES**

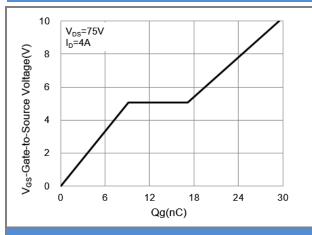


Fig.7 Gate-Charge Characteristics

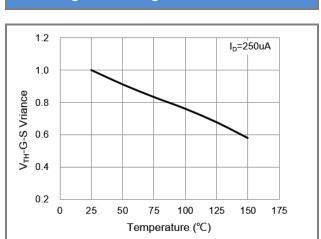
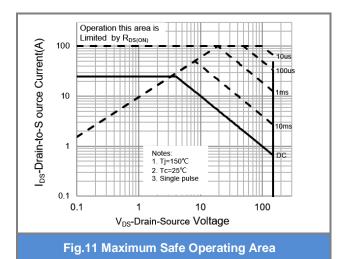


Fig.9 Threshold Voltage Variation with Temperature



1.2 | I<sub>D</sub>=250uA | 1.1 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 |

Fig.8 Breakdown Voltage Variation vs. Temperature

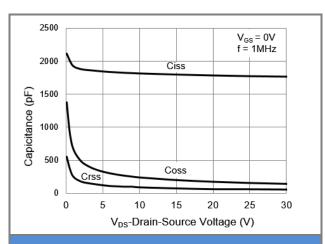


Fig.10 Capacitance vs. Drain-Source Voltage





### **TYPICAL CHARACTERISTIC CURVES**

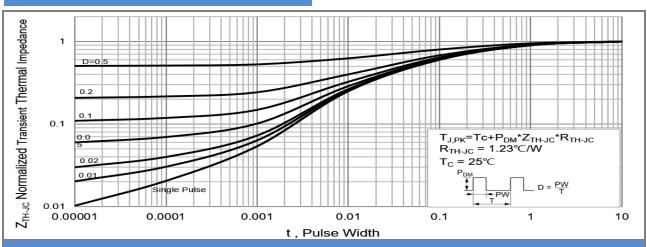
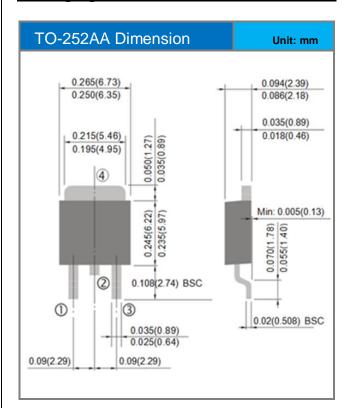


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width





### **Packaging Information**



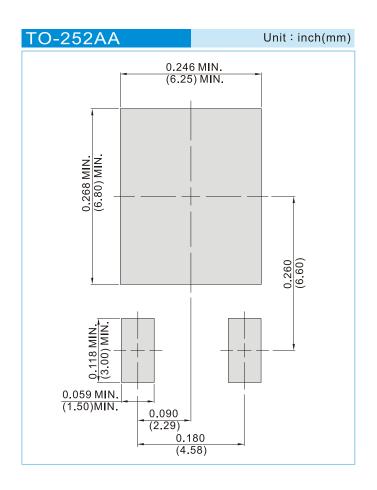




### PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJD30N15_L2_00001	TO-252AA	3,000pcs / 13" reel	D30N15	Halogen free

### **MOUNTING PAD LAYOUT**







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